

*Draw*  
gas formulation being free of  $\text{SF}_6$ , and a ratio of flow rates of  $\text{CHF}_3$ :argon:chlorine in the formulation is 5 to 80 sccm:5 to 80 sccm:5 to 60 sccm.

*D3*  
21. (Amended) An oxygen-free plasma etching gas formulation for removing an organic ARC on a metallic layer comprising more than one fluorine-containing compound, an optional inert carrier gas, and chlorine, the gas formulation being free of  $\text{SF}_6$ .